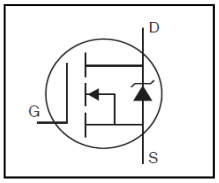
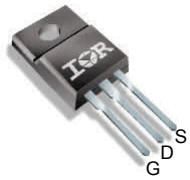
- Logic –Level Gate Drive
- Advanced Process Technology
- Ultra Low On-Resistance
- Isolated Package
- High Voltage Isolation = 2.5KVRMS ⑤
- Sink to Lead Creepage Dist. = 4.8mm
- Fully Avalanche Rated
- Lead-Free

HEXFET® Power MOSFET




| | |
|---|---|
| $V_{DSS}$ | 100V |
| $R_{DS(on)}$ | 0.026Ω |
| $I_D$ | 31A |




TO-220 Full-Pak

| G | D | S |
|---|---|---|
| Gate | Drain | Source |

**Description**

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The TO-220 Full Pak eliminates the need for additional insulating hardware in commercial-industrial applications. The molding compound used provides a high isolation capability and a low thermal resistance between the tab and external heat sink. This isolation is equivalent to using a 100 micron mica barrier with standard TO-220 product. The Fullpak is mounted to a heat sink using a single clip or by a single screw fixing.

| Base Part Number | Package Type | Standard Pack | | Orderable Part Number |
|---|---|---|---|---|
| | | Form | Quantity | |
| IRLI2910PbF | TO-220 Full-Pak | Tube | 50 | IRLI2910PbF |

| Absolute Maximum Ratings | | | |
|---|---|---|---|
| **Symbol** | **Parameter** | **Max.** | **Units** |
| $I_D$ @ $T_C$ = 25°C | Continuous Drain Current, $V_{GS}$ @ 10V | 31 | A |
| $I_D$ @ $T_C$ = 100°C | Continuous Drain Current, $V_{GS}$ @ 10V | 22 | |
| $I_{DM}$ | Pulsed Drain Current ①⑥ | 190 | |
| $P_D$ @$T_C$ = 25°C | Maximum Power Dissipation | 63 | W |
| | Linear Derating Factor | 0.42 | W/°C |
| $V_{GS}$ | Gate-to-Source Voltage | ± 16 | V |
| $E_{AS}$ | Single Pulse Avalanche Energy (Thermally Limited) ②⑥ | 520 | mJ |
| $I_{AR}$ | Avalanche Current ①⑥ | 29 | A |
| $E_{AR}$ | Repetitive Avalanche Energy ① | 6.3 | mJ |
| dv/dt | Peak Diode Recovery dv/dt③⑥ | 5.0 | V/ns |
| $T_J$<br>$T_{STG}$ | Operating Junction and<br>Storage Temperature Range | -55 to + 175 | °C |
| | Soldering Temperature, for 10 seconds (1.6mm from case) | 300 | |
| | Mounting torque, 6-32 or M3 screw | 10 lbf•in (1.1N•m) | |

**Thermal Resistance**

| Symbol | Parameter | Typ. | Max. | Units |
|---|---|---|---|---|
| $R_{\theta JC}$ | Junction-to-Case | — | 2.4 | °C/W |
| $R_{\theta JA}$ | Junction-to-Ambient | — | 65 | |

**Electrical Characteristics @ $T_J$ = 25°C (unless otherwise specified)**

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|---|---|---|---|---|---|---|
| $V_{(BR)DSS}$ | Drain-to-Source Breakdown Voltage | 100 | — | — | V | $V_{GS}$ = 0V, $I_D$ = 250µA |
| $\Delta V_{(BR)DSS}/\Delta T_J$ | Breakdown Voltage Temp. Coefficient | — | 0.12 | — | V/°C | Reference to 25°C, $I_D$ = 1mA ⑥ |
| $R_{DS(on)}$ | Static Drain-to-Source On-Resistance | — | — | 0.026 | Ω | $V_{GS}$ = 10V, $I_D$ = 16A |
| | | — | — | 0.030 | | $V_{GS}$ = 5.0V, $I_D$ = 16A |
| | | — | — | 0.040 | | $V_{GS}$ = 4.0V, $I_D$ = 14A |
| $V_{GS(th)}$ | Gate Threshold Voltage | 1.0 | — | 2.0 | V | $V_{DS}$ = $V_{GS}$, $I_D$ = 250µA |
| gfs | Forward Trans conductance | 28 | — | — | S | $V_{DS}$ = 50V, $I_D$ = 29A⑥ |
| $I_{DSS}$ | Drain-to-Source Leakage Current | — | — | 25 | µA | $V_{DS}$ = 100V, $V_{GS}$ = 0V |
| | | — | — | 250 | | $V_{DS}$ = 80V,$V_{GS}$ = 0V,$T_J$ =150°C |
| $I_{GSS}$ | Gate-to-Source Forward Leakage | — | — | 100 | nA | $V_{GS}$ = 16V |
| | Gate-to-Source Reverse Leakage | — | — | -100 | | $V_{GS}$ = -16V |
| $Q_g$ | Total Gate Charge | — | — | 140 | nC | $I_D$ = 29A |
| $Q_{gs}$ | Gate-to-Source Charge | — | — | 20 | | $V_{DS}$ = 80V |
| $Q_{gd}$ | Gate-to-Drain Charge | — | — | 81 | | $V_{GS}$ = 5.0V , See Fig. 6 and 13④⑥ |
| $t_{d(on)}$ | Turn-On Delay Time | — | 11 | — | ns | $V_{DD}$ = 50V |
| $t_r$ | Rise Time | — | 100 | — | | $I_D$ = 29A |
| $t_{d(off)}$ | Turn-Off Delay Time | — | 49 | — | | $R_G$= 1.4Ω,$V_{GS}$ = 5.0V |
| $t_f$ | Fall Time | — | 55 | — | | $R_D$= 1.7Ω, See Fig. 10④⑥ |
| $L_D$ | Internal Drain Inductance | — | 4.5 | — | nH | Between lead, 6mm (0.25in.) from package and center of die contact |
| $L_S$ | Internal Source Inductance | — | 7.5 | — | | |
| $C_{iss}$ | Input Capacitance | — | 3700 | — | pF | $V_{GS}$ = 0V |
| $C_{oss}$ | Output Capacitance | — | 630 | — | | $V_{DS}$ = 25V |
| $C_{rss}$ | Reverse Transfer Capacitance | — | 330 | — | | $f$ = 1.0MHz, See Fig. 5⑥ |
| C | Drain to Sink Capacitance | — | 12 | — | | $f$ = 1.0MHz |

**Source-Drain Ratings and Characteristics**

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|---|---|---|---|---|---|---|
| $I_S$ | Continuous Source Current (Body Diode) | — | — | 31 | A | MOSFET symbol showing the integral reverse p-n junction diode. |
| $I_{SM}$ | Pulsed Source Current (Body Diode) ①⑥ | — | — | 190 | | |
| $V_{SD}$ | Diode Forward Voltage | — | — | 1.3 | V | $T_J$ = 25°C,$I_S$ = 16A,$V_{GS}$ = 0V ④ |
| $t_{rr}$ | Reverse Recovery Time | — | 240 | 350 | ns | $T_J$ = 25°C ,$I_F$ = 29A |
| $Q_{rr}$ | Reverse Recovery Charge | — | 1.8 | 2.7 | µC | di/dt = 100A/µs ④⑥ |

**Notes:**

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
② $V_{DD}$ = 25V, starting $T_J$ = 25°C, L = 1.2mH, $R_G$ = 25Ω, $I_{AS}$ = 29A (See fig. 12)
③ $I_{SD}$ ≤ 29A, di/dt ≤ 490A/µs, $V_{DD}$ ≤ $V_{(BR)DSS}$, $T_J$ ≤ 175°C.
④ Pulse width ≤ 300µs; duty cycle ≤ 2%.
⑤ t=60s, $f$=60Hz
⑥ Uses IRL2910 data and test conditions.

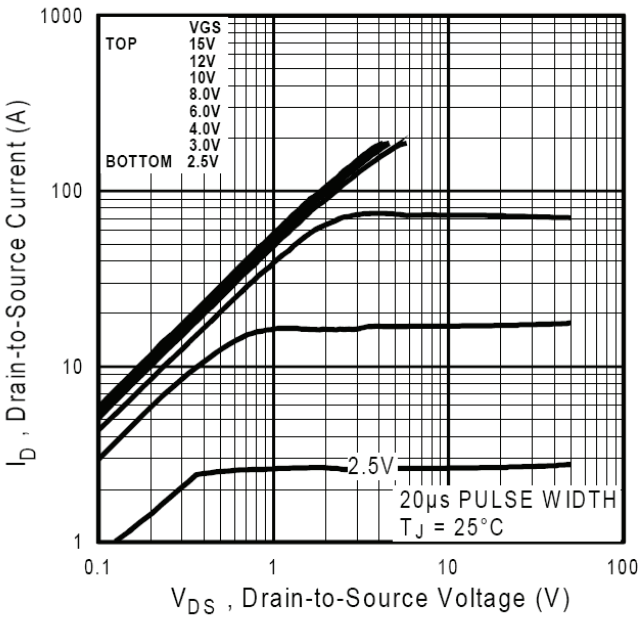



**Fig. 1** Typical Output Characteristics

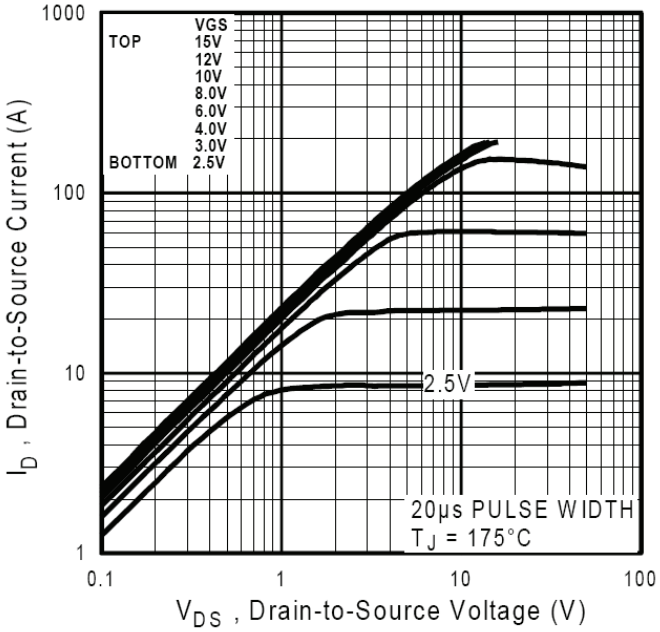



**Fig. 2** Typical Output Characteristics

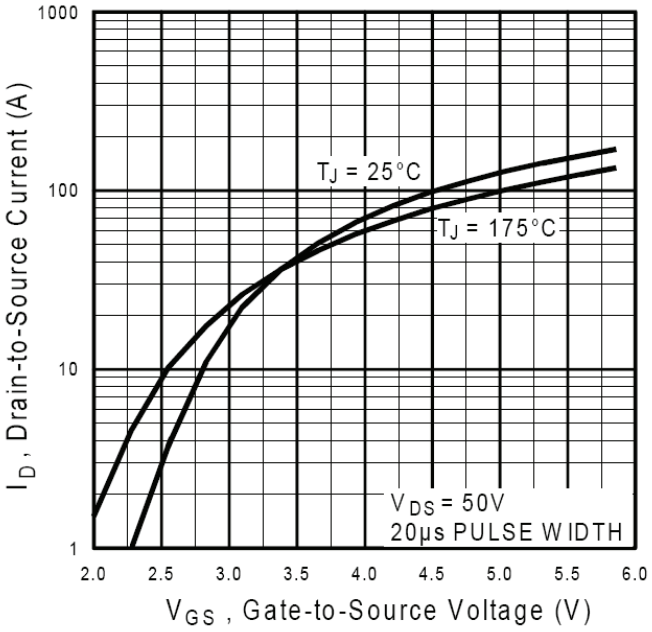



**Fig. 3** Typical Transfer Characteristics

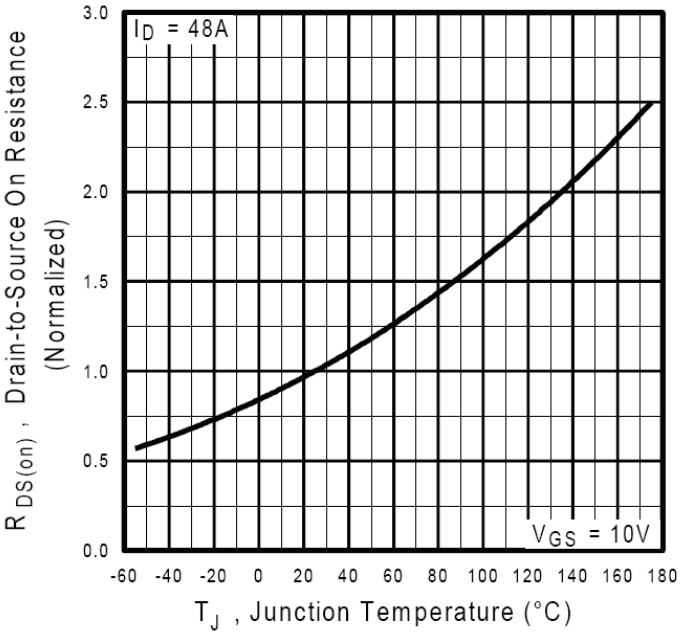



**Fig. 4** Normalized On-Resistance vs. Temperature

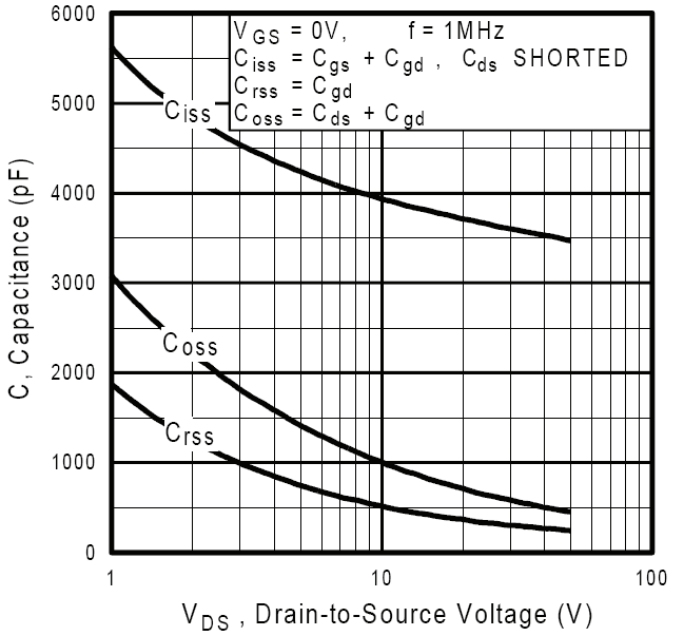



**Fig 5.** Typical Capacitance vs. Drain-to-Source Voltage

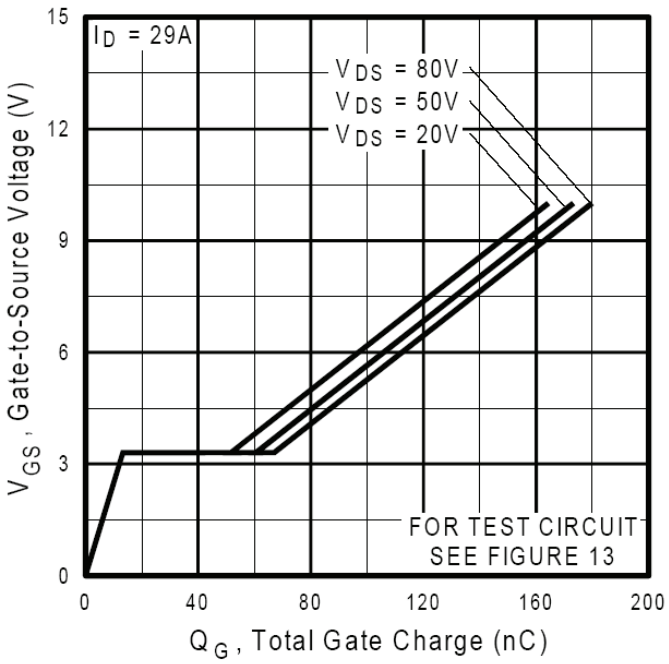



**Fig 6.** Typical Gate Charge vs. Gate-to-Source Voltage

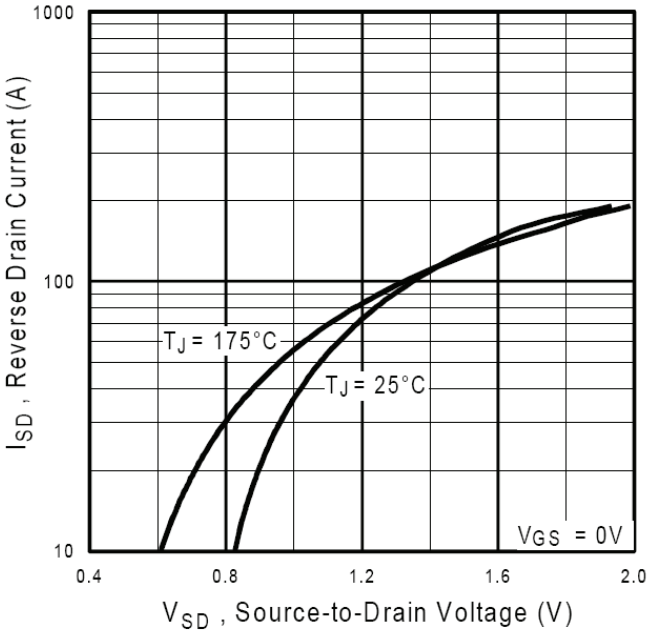



**Fig. 7** Typical Source-to-Drain Diode Forward Voltage

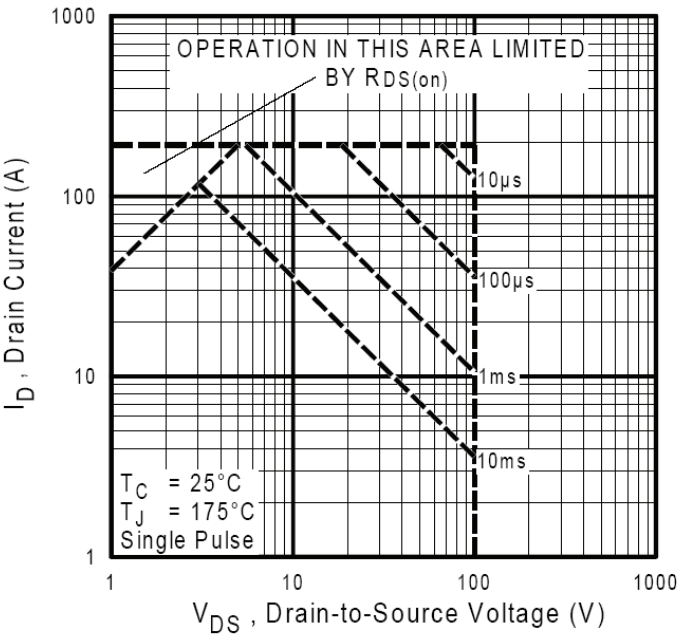



**Fig 8.** Maximum Safe Operating Area

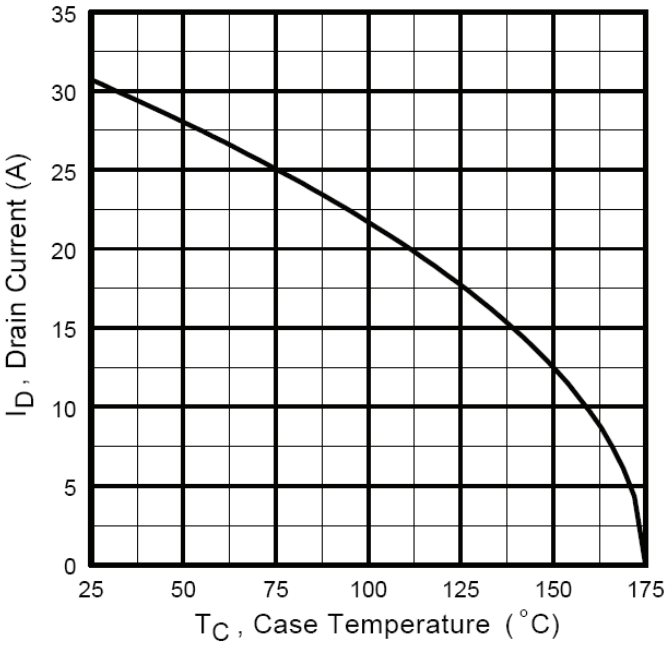



**Fig 9.** Maximum Drain Current vs. Case Temperature

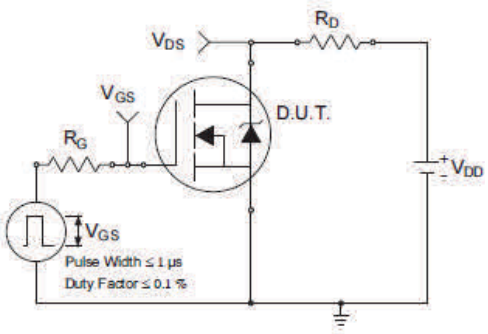



**Fig 10a.** Switching Time Test Circuit

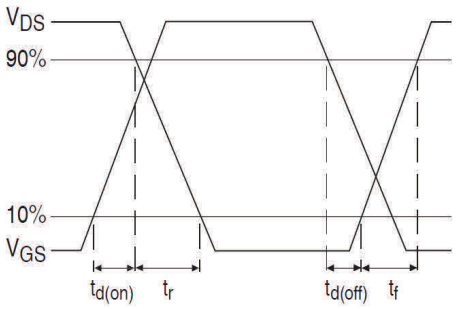



**Fig 10b.** Switching Time Waveforms

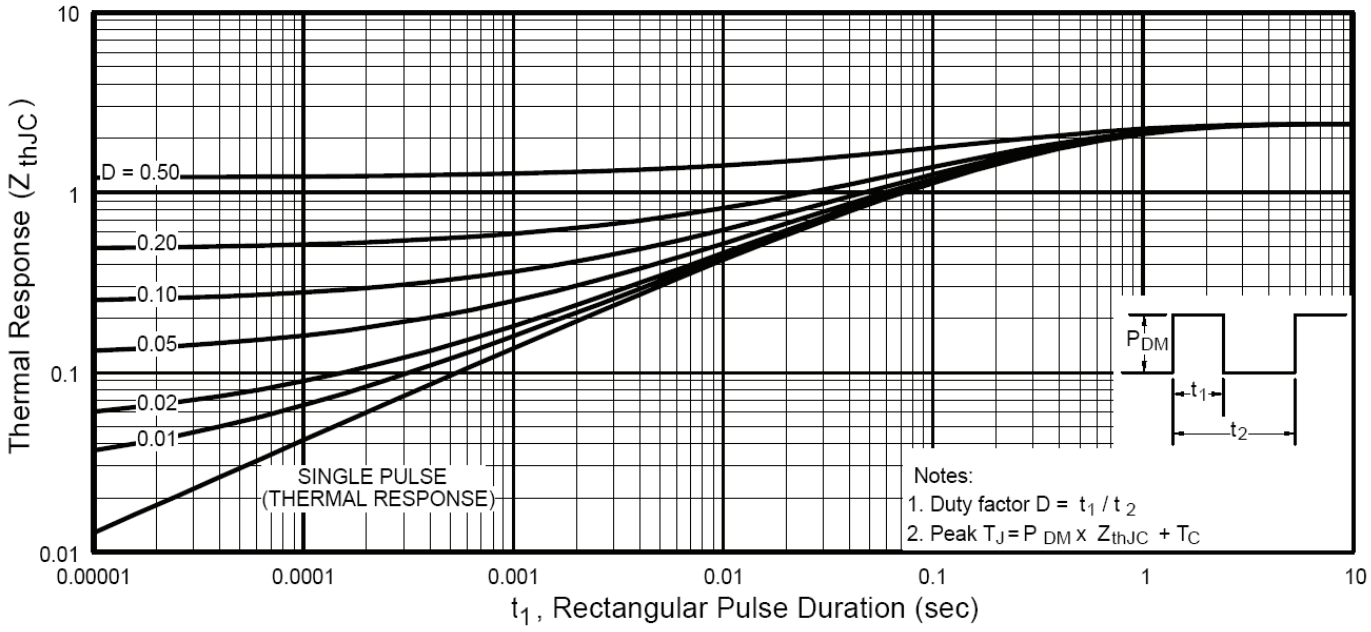



**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

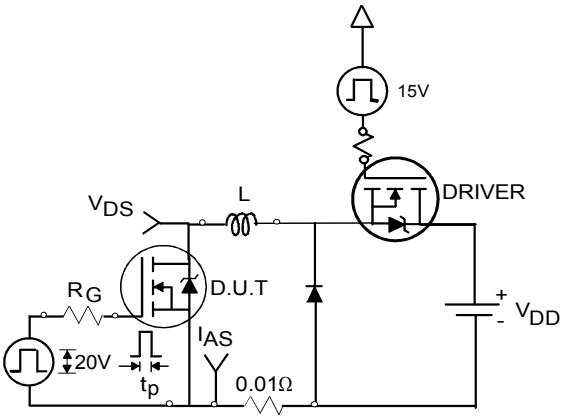



**Fig 12a.** Unclamped Inductive Test Circuit

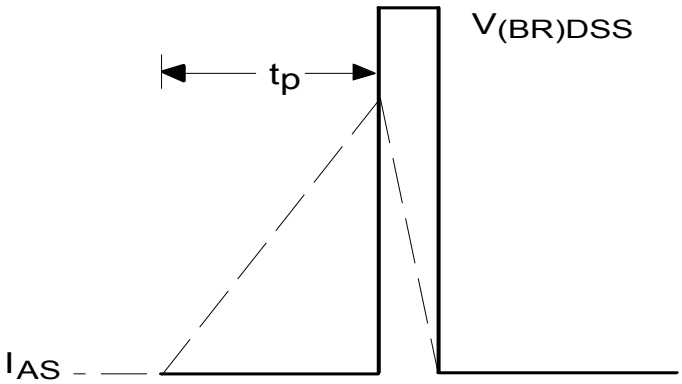



**Fig 12b.** Unclamped Inductive Waveforms

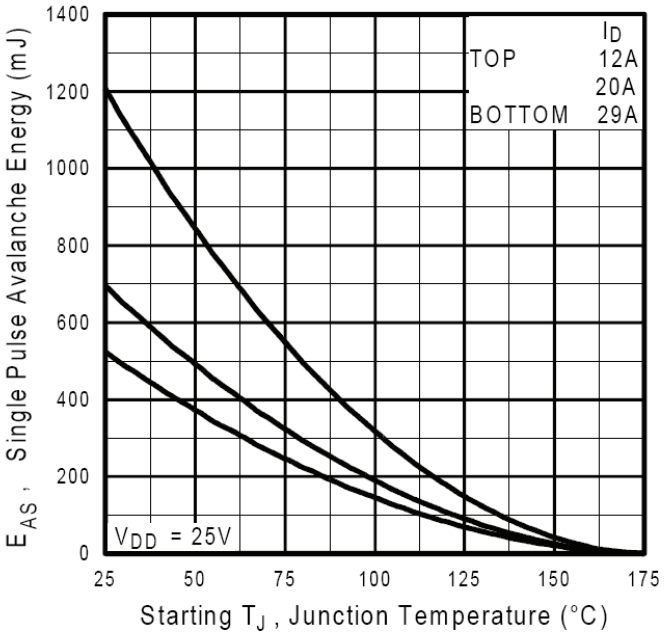



**Fig 12c.** Maximum Avalanche Energy vs. Drain Current

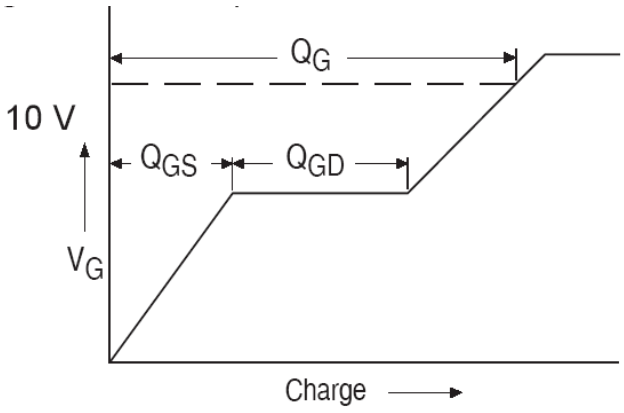



**Fig 13a.** Gate Charge Waveform

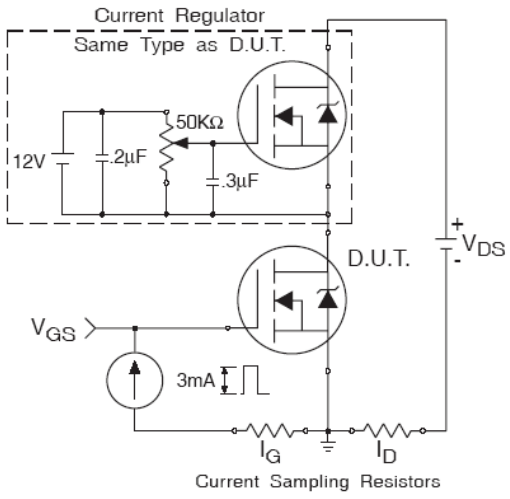



**Fig 13b.** Gate Charge Test Circuit

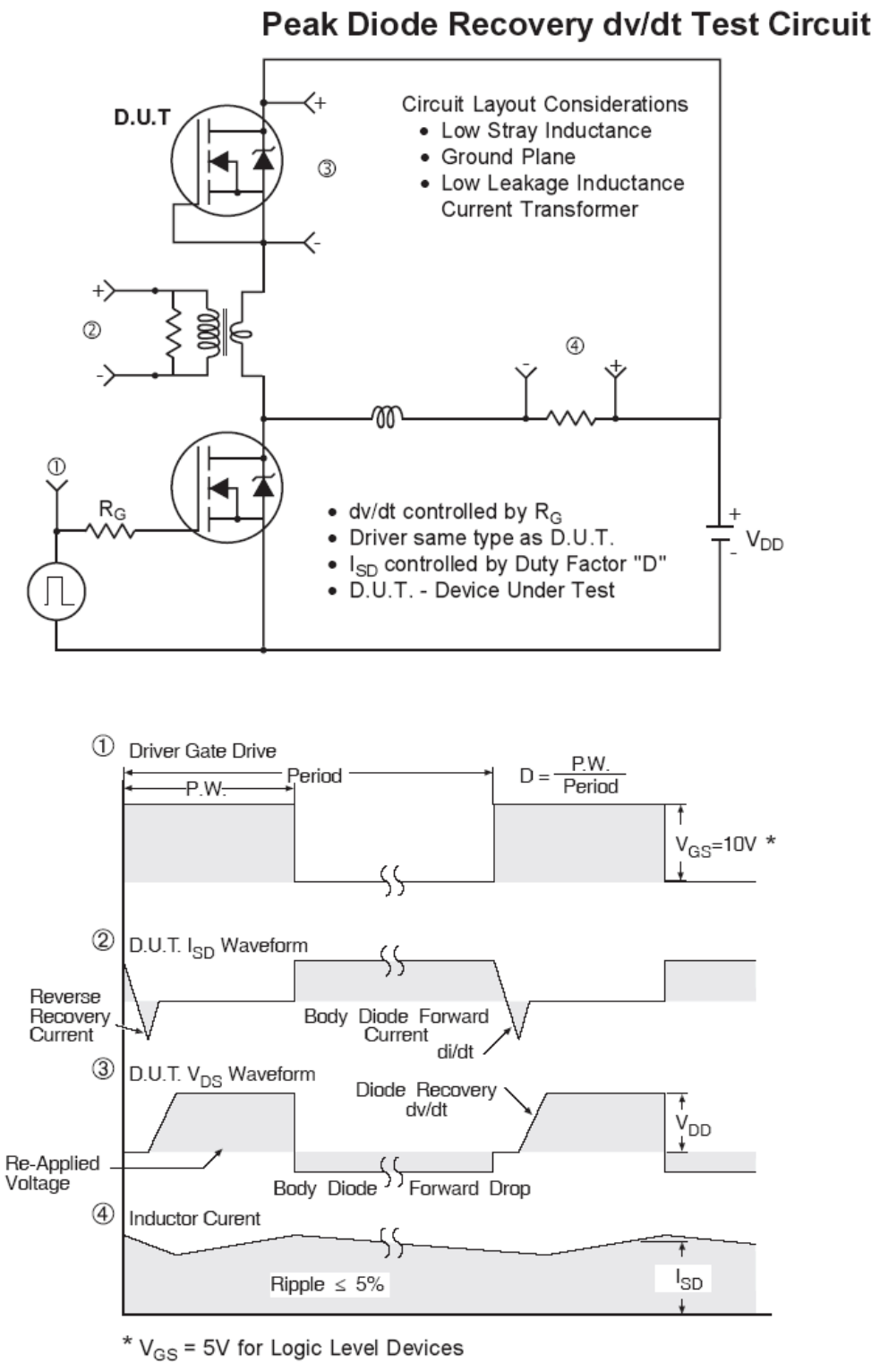
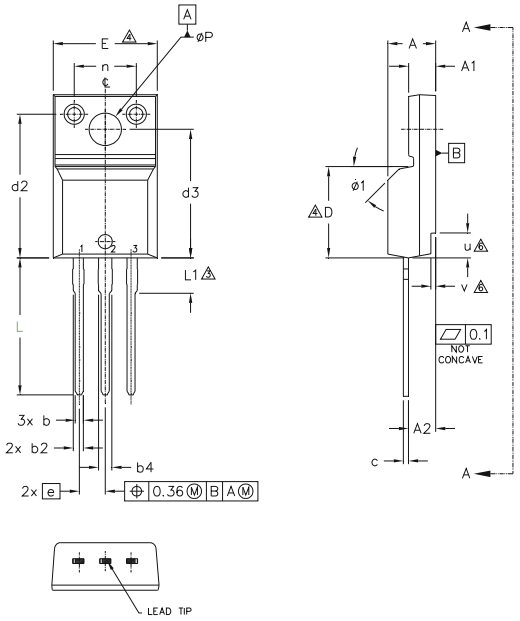



**Fig 14.** Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

**TO-220 Full-Pak Package Outline** (Dimensions are shown in millimeters (inches))




NOTES:

1.0 DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M– 1994.

2.0 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].

3.0 LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.

4.0 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTER MOST EXTREMES OF THE PLASTIC BODY.

5.0 DIMENSION b1, b3, b5 & c1 APPLY TO BASE METAL ONLY.

6.0 STEP OPTIONAL ON PLASTIC BODY DEFINED BY DIMENSIONS u & v.

7.0 CONTROLLING DIMENSION : INCHES.

| SYMBOL | DIMENSIONS | | | | NOTES |
|---|---|---|---|---|---|
| | MILLIMETERS | | INCHES | | |
| | MIN. | MAX. | MIN. | MAX. | |
| A | 4.57 | 4.83 | .180 | .190 | |
| A1 | 2.57 | 2.82 | .101 | .111 | |
| A2 | 2.51 | 2.92 | .099 | .115 | |
| b | 0.61 | 0.94 | .024 | .037 | |
| b1 | 0.61 | 0.89 | .024 | .035 | 5 |
| b2 | 0.76 | 1.27 | .030 | .050 | |
| b3 | 0.76 | 1.22 | .030 | .048 | 5 |
| b4 | 1.02 | 1.52 | .040 | .060 | |
| b5 | 1.02 | 1.47 | .040 | .058 | 5 |
| c | 0.33 | 0.63 | .013 | .025 | |
| c1 | 0.33 | 0.58 | .013 | .023 | 5 |
| D | 8.66 | 9.80 | .341 | .386 | 4 |
| d1 | 15.80 | 16.13 | .622 | .635 | |
| d2 | 13.97 | 14.22 | .550 | .560 | |
| d3 | 12.29 | 12.93 | .484 | .509 | |
| E | 9.63 | 10.74 | .379 | .423 | 4 |
| e | 2.54 BSC | | .100 BSC | | |
| L | 13.21 | 13.72 | .520 | .540 | |
| L1 | 3.10 | 3.68 | .122 | .145 | 3 |
| n | 6.05 | 6.60 | .238 | .260 | |
| øP | 3.05 | 3.45 | .120 | .136 | |
| u | 2.39 | 2.49 | .094 | .098 | 6 |
| v | 0.41 | 0.51 | .016 | .020 | 6 |
| ø1 | – | 45° | – | 45° | |

LEAD ASSIGNMENTS

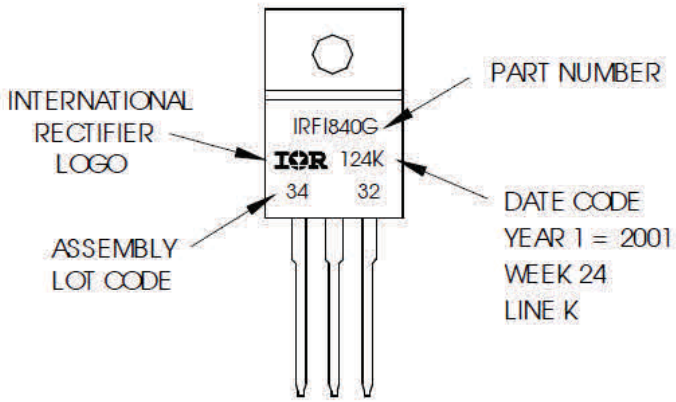
HEXFET
1.– GATE
2.– DRAIN
3.– SOURCE

IGBTs, CoPACK
1.– GATE
2.– COLLECTOR
3.– EMITTER

**TO-220 Full-Pak Part Marking Information**

EXAMPLE: THIS IS AN IRFI840G
WITH ASSEMBLY
LOT CODE 3432
ASSEMBLED ON WW 24, 2001
IN THE ASSEMBLY LINE "K"

Note: "P" in assembly line position
indicates "Lead-Free"




TO-220AB Full-Pak packages are not recommended for Surface Mount Application.

Note: For the most current drawing please refer to website at http://www.irf.com/package/

## Qualification Information

| | | |
|---|---|---|
| **Qualification Level** | Industrial (per JEDEC JESD47F) † | |
| **Moisture Sensitivity Level** | TO-220 Full-Pak | N/A |
| **RoHS Compliant** | Yes | |

† Applicable version of JEDEC standard at the time of product release.

## Revision History

| Date | Comments |
|---|---|
| 04/27/2017 | • Changed datasheet with Infineon logo - all pages.<br>• Corrected Package Outline on page 8.<br>• Added disclaimer on last page. |
| 08/22/17 | • Updated typo for Vgsth max value from 4.0V to 2.0V-page2 |



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